BLP8G27-5

Power LDMOS transistor

Rev. 2 — 1 October 2015

AMPLEON

Product data sheet

1. Product profile

1.1 General description

5 W plastic LDMOS power transistor for base station applications at frequencies from 700 MHz to 2700 MHz.

Table 1. Application performance (multiple frequencies)

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 55 mA; in a class-AB application circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(dBm)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2700	55	28	28.8	19	19	-50

^[1] Test signal: 2-carrier W-CDMA; test model 1; 10 MHz carrier spacing (mode 101); PAR = 8.3 dB at 0.01% probability on CCDF (46 % clipping).

1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for broadband operation
- Excellent thermal stability
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- CDMA
- W-CDMA
- GSM EDGE
- MC-GSM
- LTE
- WiMAX

Power LDMOS transistor

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol [1]
1, 2, 5, 6, 7, 8, 9, 10, 11, 12, 15, 16	n.c.	16 9	13, 14
3, 4	gate		
13, 14	drain		3, 4 — ← exposed
exposed die-pad	source [2]	<u> </u>	die-pad
		Transparent top view	aaa-017948

- [1] To be used in single ended applications only.
- [2] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package	ackage		
	Name	Description	Version	
BLP8G27-5		plastic thermal enhanced very thin small outline package; no leads;16 terminals; body 4 \times 6 \times 0.85 mm	SOT1371-1	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 80 °C; P _L = 1 W	6.4	K/W

Power LDMOS transistor

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.09 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 9 \text{ mA}$	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-1.4	-	+1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	1.6	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_{D} = 9 \text{ mA}$	-	80	-	mS
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}; I_D = 315 \text{ mA}$	-	2	-	Ω

Table 7. RF characteristics

A derivative functional RF test is performed in production. The performance as mentioned below is verified by design and characterization in an NXP class-AB application board.

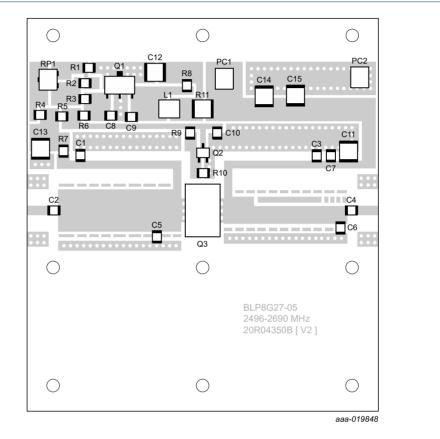
Test signal: pulsed CW; δ = 10%; t_p = 100 μ s; V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; f = 2140 MHz

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 0.75 W$	17	18	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 0.75 W	15	17	-	%
P _{L(1dB)}	output power at 1 dB gain compression		5	-	-	W

Power LDMOS transistor

7. Application information

7.1 Application circuit



Printed-Circuit Board (PCB): Rogers RO4350B; ϵ_{r} = 3.5; thickness = 0.508 mm; thickness copper plating = 35 μ m.

See Table 8 for list of components.

Fig 1. Component layout

Table 8. List of componentsSee Figure 1 for component layout.

Component	Description	Value	Remarks
C1, C2, C3, C4	multilayer ceramic chip capacitor	12 pF	ATC 100A
C5	multilayer ceramic chip capacitor	3 pF	ATC 100A
C6	multilayer ceramic chip capacitor	1.9 pF	ATC 100A
C7, C8, C9, C10	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: GRM21BR71H104KA01L
C11, C12, C13	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata: GRM32ER71H475KA88L
C14, C15	multilayer ceramic chip capacitor	10 μF	AVX
RP1	potentiometer	10 turns	
R1	chip resistor	75 Ω	SMD 0805

Power LDMOS transistor

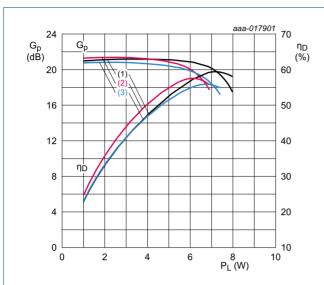
Table 8. List of components ...continued See Figure 1 for component layout.

Component	Description	Value	Remarks
R2, R3	chip resistor	430 Ω	SMD 0805
R4	chip resistor	2 kΩ	SMD 0805
R5	chip resistor	11 kΩ	SMD 0805
R6	chip resistor	1.1 kΩ	SMD 0805
R7	chip resistor	2.0 kΩ	SMD 0805
R8	chip resistor	9.1 Ω	SMD 0805
R9	chip resistor	5.1 Ω	SMD 0805
R10	chip resistor	910 Ω	SMD 0805
R11	chip resistor	500 Ω, 1/4 W	leaded
L1	ferrite bead	1 μF, 50 V	Murata: GRM31MR71H105KA88L
Q1	surface-mounted package	-	SOT89
Q2	transistor	-	PMBT2222A
Q3	transistor	-	BLP8G27-5
PC1	power connector	-	positive supply
PC2	power connector	-	negative supply

Power LDMOS transistor

7.2 Graphical data

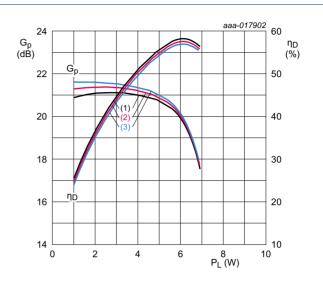
7.2.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; δ = 10 %; t_{o} = 100 μs .

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

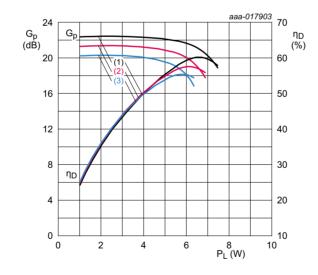
Fig 2. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; T_{case} = 25 °C; f = 2140 MHz; δ = 10 %; t_{p} = 100 μ s.

- (1) $I_{Dq} = 45 \text{ mA}$
- (2) $I_{Dq} = 55 \text{ mA}$
- (3) $I_{Dq} = 65 \text{ mA}$

Fig 3. Power gain and drain efficiency as function of output power; typical values

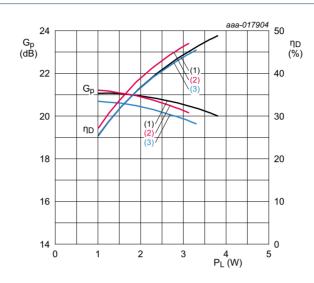


 V_{DS} = 28 V; I_{Dq} = 55 mA; f = 2140 MHz; δ = 10 %; t_p = 100 $\mu s.$

- (1) $T_{case} = -37 \, ^{\circ}C$
- (2) $T_{case} = +25 \, ^{\circ}C$
- (3) $T_{case} = +85 \, ^{\circ}C$

Fig 4. Power gain and drain efficiency as function of output power; typical values

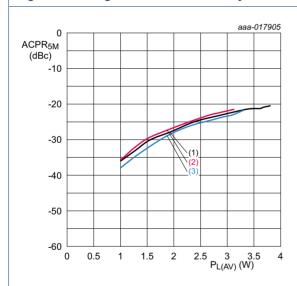
7.2.2 2-Carrier W-CDMA



V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

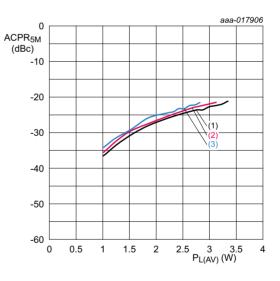
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values



 V_{DS} = 28 V; I_{Dq} = 55 mA; f = 2140 MHz; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) $T_{case} = -37 \, ^{\circ}C$
- (2) $T_{case} = +25 \, ^{\circ}C$
- (3) $T_{case} = +85 \, ^{\circ}C$

Fig 7. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values

Power LDMOS transistor

8. Test information

8.1 Ruggedness in class-AB operation

The BLP8G27-5 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 55 mA; P_L = 1 W; frequency from 700 MHz to 2700 MHz.

8 of 13

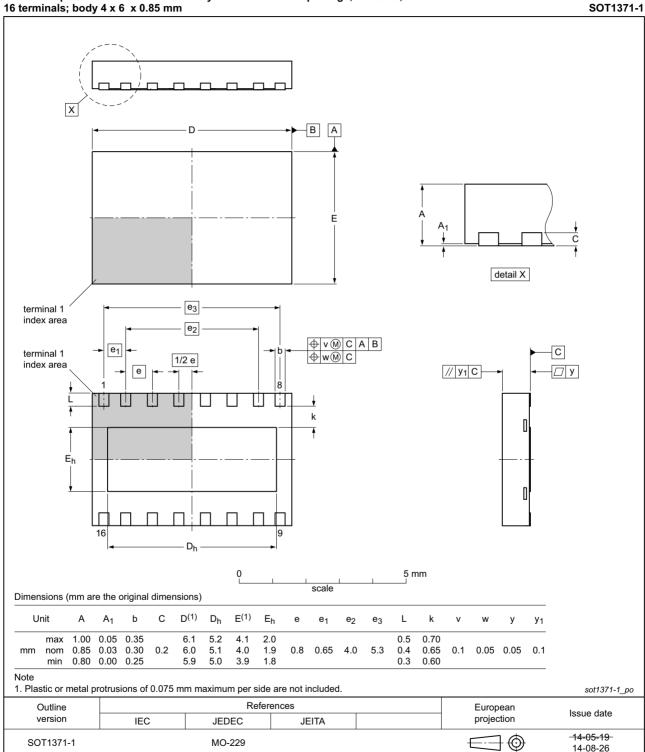
BLP8G27-5 AMPLEON

Power LDMOS transistor

Package outline

HVSON16: plastic thermal enhanced very thin small outline package; no leads;

SOT1371-1



Package outline SOT1371-1 (HVSON16) Fig 8.

Power LDMOS transistor

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 9. Abbreviations

Acronym	Description	
CCDF	Complementary Cumulative Distribution Function	
CDMA	Code Division Multiple Access	
CW	Continuous Wave	
EDGE	Enhanced Data rates for GSM Evolution	
ESD	ElectroStatic Discharge	
GSM	Global System for Mobile Communication	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
LTE	Long Term Evolution	
MC-GSM	Multi Carrier GSM	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VSWR	Voltage Standing-Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	
WiMAX	Worldwide Interoperability for Microwave Access	

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP8G27-5 v.2	20151001	Product data sheet	-	BLP8G27-5 v.1
Modifications:	The format of this document has been redesigned to comply with the new identity guidelines of Ampleon			
	Legal texts have been adapted to the new company name where appropriate			
BLP8G27-5 v.1	20150915	Product data sheet	-	-

Power LDMOS transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an

Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at http://www.ampleon.com/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

BLP8G27-

All information provided in this document is subject to legal disclaimers.

Power LDMOS transistor

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon' standard warranty and Ampleon' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks.

14. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

AMPLEON

BLP8G27-5

Power LDMOS transistor

15. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 2
6	Characteristics 3
7	Application information 4
7.1	Application circuit 4
7.2	Graphical data 6
7.2.1	Pulsed CW 6
7.2.2	2-Carrier W-CDMA
8	Test information 8
8.1	Ruggedness in class-AB operation 8
9	Package outline
10	Handling information 10
11	Abbreviations
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions 11
13.3	Disclaimers
13.4	Trademarks 12
14	Contact information 12
15	Contents 13

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.